tions in the filled skutterudites are due mostly to the fraction of the rare-earth sites that remain empty in samples prepared using equilibrium-synthesis methods. A simple semiconductor-transport model successfully reproduces most of the qualitative features of the resistivity and Seebeck data from these materials. By varying the extrinsic carrier concentration in the filled skutterudites, this model yields a maximum value for ZT of 1.4 at 1000 K and a maximum ZT value of 0.3 at 300 K.

The filled-skutterudite antimonides have demonstrated the validity of the "electron-crystal, phonon-glass" idea in the design of new thermoelectric materials for operation at elevated temperatures. There are many other crystal structures and compounds that contain atomic cages large enough to incorporate additional atoms. It is believed that the filled-skutterudite antimonides only represent a small fraction of a more general class of "rattling semiconductors" and that some of these materials will undoubtedly have high values for ZT at and below room temperature.

Acknowledgments

It is a pleasure to acknowledge useful discussions with D.G. Mandrus and G.D. Mahan, and to thank D.P. Norton for carefully reading and editing the manuscript. Research was sponsored in part by a Cooperative Research and Development Agreement with Marlow Industries, and in part by the Division of Materials Sciences, U.S. Department of Energy Contract No. DE-AC05-96OR22464. Oak Ridge National Laboratory is managed by the Lockheed-Martin Energy Research Corporation.

References

- 1. D.M. Rowe, ed., CRC Handbook of Thermoelectrics (Chemical Rubber, Boca Raton, FL, 1995).
- 2. G.D. Mahan, in Solid State Physics, edited

by H. Ehrenreich and F. Spaepen (Academic Press, Inc., New York, 1997).

 C. Wood, Rep. Prog. Phys. 51 (1988) p. 459.
 G.D. Mahan, B.C. Sales, and J.W. Sharp, Phys. Today (1997) p. 42.

5. B.C. Sales, Current Opinion in Solid State and Materials Sciences 2 (1997) p. 284.

6. G.A. Slack, in *CRC Handbook of Thermo-electrics*, edited by D.M. Rowe (Chemical Rubber, Boca Raton, FL, 1995) p. 407.

7. *Ibid.*, in *Solid State Physics*, vol. 34, edited by H. Ehrenreich, F. Seitz, and D. Turnbull (Academic Press, Inc., New York, 1979) p. 1. 8. D.G. Cahill, S.K. Watson, and R.O. Pohl,

Phys. Rev. B 46 (1992) p. 6131. 9. W. Jeitschko and D.J. Braun, Acta Crystal-

logr. Sec. B **33** (1977) p. 3401.

10. D.J. Braun and W. Jeitschko, J. Less-Common Metals **76** (1980) p. 147.

Ibid., J. Solid State Chem. 32 (1980) p. 357.
 Ibid., J. Less-Common Metals 76 (1980) p. 33.

13. B.C. Chakoumakos, private communication.

14. N.T. Stetson, S.M. Kauzlarich, and H. Hope. J. Solid State Chem. 91 (1991) p. 140.

15. L.E. DeLong and G.P. Meisner, Solid State Commun. 53 (1985) p. 119.

16. D.T. Morelli and G.P. Meisner, J. Appl. Phys. 77 (1995) p. 3777.

17. G.P. Meisner, M.S. Torikachvili, K.N. Yang, M.B. Maple, and R.P. Guertin, *ibid.* 57 (1985) p. 3073.

M.E. Danebrock, C.B.H. Evers, and W. Jeitschko, *J. Phys. Chem. Solids* **57** (1996) p. 381.
 G.P. Meisner, *Physica* **108B** (1981) p. 763.

20. S. Zemi, D. Tranqui, P. Chaudouet, R. Madar, and J.P. Senateur, J. Solid State Chem. **65** (1986) p. 1.

21. I. Shirotani, T. Adachi, K. Tachi, S. Todo, K. Nozawa, T. Yagi, and M. Kinoshita, *J. Phys. Chem. Solids* 57 (1996) p. 211.

22. B.C. Sales, D. Mandrus, and R.K. Williams, *Science* **272** (1996) p. 1325.

23. G.S. Nolas, G.A. Slack, D.T. Morelli, T.M. Tritt, and A.C. Ehrlich, *J. Appl. Phys.* **79** (1996) p. 4002.

24. T.M. Tritt, G.S. Nolas, G.A. Slack, A.C. Ehrlich, D.J. Gillespie, and J.L. Cohn, *ibid.* p. 8412.

p. 8412. 25. J-P. Fleurial, A. Borshchevsky, T. Caillat, D.T. Morelli, and G.P. Meisner, in *Proc. 15th Int. Conf. on Thermoelectrics* (IEEE, Piscataway, NJ, 1996) p. 91. 26. B. Chen, J.H. Xu, C. Uher, D.T. Morelli, G.P. Meisner, J-P. Fleurial, T. Caillat, and A. Borshchevsky, *Phys. Rev. B* **55** (1997) p. 1476.
27. D. Mandrus, B.C. Sales, V. Keppens, B.C. Chakoumakos, P. Dai, L.A. Boatner, R.K. Williams, T.W. Darling, A. Migliori, M.B. Maple, D.A. Gajewski, and E.J. Freeman, in *Thermoelectric Materials: New Directions and Approaches*, edited by T.M. Tritt, G. Mahan, H.B. Lyon, and M.G. Kanatzidis (Mater. Res. Soc. Symp. Proc. **478**, Pittsburgh, 1997).

28. B.C. Sales, D. Mandrus, B.C. Chakoumakos, V. Keppens, and J.R. Thompson, *Phys. Rev. B* **56** (in press).

V. Keppens (private communication).
 A.J. Sievers, *Phys. Rev. Lett.* 13 (1965) p. 310.
 A.D. Caplin, G. Gruner, and J.B. Dunlap, *ibid.* 30 (1973) p. 1138.

32. G.S. Nolas, G.A. Slack, T. Caillat, and G.P. Meisner, *J. Appl. Phys.* **79** (1996) p. 2622.

33. C. Kittel, *Introduction to Solid State Physics* (John Wiley & Sons, Inc., New York, 1968) p. 186.

34. H.J. Goldsmid, *Electronic Refrigeration* (Pion Limited, London, 1986) p. 29.

35. T. Caillat, A. Borshchevsky, and J-P. Fleurial, *Proc. 11th Int. Conf. on Thermoelectrics*, edited by K.R. Rao (University of Texas Press, Arlington, 1993) p. 98.

36. J.W. Sharp, E.C. Jones, R.K. Williams, P.M. Martin, and B.C. Sales, *J. Appl. Phys.* **78** (1995) p. 1013.

37. D. Singh and I.I. Mazin, *Phys. Rev. B* **56** (1997) p. 1650.

Brian C. Sales is a co-group leader of the Novel Materials Group in the Solid State Division at the Oak Ridge National Laboratory. He received a PhD degree from the University of California—San Diego. His research concerns the synthesis and characterization of unusual electronic, magnetic, and optical materials. His current interests include novel phosphate glasses, high-temperature superconductors, extended electron compounds, quantum magnetism in low-dimensional systems, and the development of thermoelectric materials with improved efficiencies. Sales can be reached at the following e-mail address: vb4@ornl.gov.

Advertisers in This Issue			
	Page No.		Page No.
Advanced Research Instruments Corp.	6	Materials Research Society	Inside back cover
Andeen-Hagerling Inc.	10	Multiwire Laboratories, Ltd.	47
Bruker Analytical X-Ray Systems	3, 5	Radiant Technologies, Inc.	10
Chemat Technology Inc.	8	Society of Vacuum Coaters	9
EDAX International Inc.	42	Virginia Semiconductors Inc.	47
High Voltage Engineering	Inside front cover	Voltaix Inc.	7
Huntington Laboratories	Outside back cover	John Wiley & Sons, Inc.	48